



APT28M120B2 Information



For Reference Only

Part Number APT28M120B2

Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 29A T-MAX

Package TO-247-3 Variant

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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APT28M120B2 Specifications

Manufacturer Part Number APT28M120B2 Manufacturer Microsemi Corporation Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Variant Series POWER MOS 8? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 29A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 300nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1135W (Tc) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3 VariantSeriesPOWER MOS 8?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C29A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs300nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1135W (Tc)Rds On (Max) @ Id, Vgs560 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Manufacturer Part Number	APT28M120B2
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SeriesPOWER MOS 8?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C29A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs300nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1135W (Tc)Rds On (Max) @ Id, Vgs560 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C29A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs300nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1135W (Tc)Rds On (Max) @ Id, Vgs560 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Package	TO-247-3 Variant
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 29A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package T-MAX? [B2] Package / Case MOSFET (Metal Oxide) 1200V 1200V 1200V 129A (Tc) 10V 9670pF @ 25V 430V 500 mOhm @ 14A, 10V 1135W (Tc) Through Hole T-MAX? [B2] Package / Case	Series	POWER MOS 8?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 29A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature Supplier Device Package T-MAX? [B2] Package / Case Package (Vas On, Min Rds On) 10V 29A (Tc) 29A (Tc)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 10put Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature Supplier Device Package T-MAX? [B2] Package / Case 29A (Tc) 40V 55°C ~ 150°C 10V 10V 11V 10V 9670pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 300nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9670pF @ 25V Vgs (Max) ### ### #### #######################	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 300nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 9670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1135W (Tc) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Current - Continuous Drain (Id) @ 25°C	29A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 9670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case 300nC @ 10V 9670pF @ 25V 250 1135W (Tc) 560 mOhm @ 14A, 10V -55°C ~ 150°C (TJ) Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs(th) (Max) @ Id	5V @ 2.5mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)1135W (Tc)Rds On (Max) @ Id, Vgs560 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Gate Charge (Qg) (Max) @ Vgs	300nC @ 10V
FET Feature - Power Dissipation (Max) 1135W (Tc) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Input Capacitance (Ciss) (Max) @ Vds	9670pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 560 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs560 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Power Dissipation (Max)	1135W (Tc)
Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Rds On (Max) @ Id, Vgs	560 mOhm @ 14A, 10V
Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3 Variant	Mounting Type	Through Hole
	Supplier Device Package	T-MAX? [B2]
Report errors?	Package / Case	TO-247-3 Variant
		Report errors?

APT28M120B2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APT28M120B2 Payment Methods



















APT28M120B2 Shipping Methods













If you have any question about APT28M120B2, please do not hesitate to contact us!

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